



N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{(BR)DSS} (V)	$r_{DS(on)}(\Omega)$	I _D (A)	Q _g (Typ)	
60	0.0055 at $V_{GS} = 10 \text{ V}$	90 ^d	78.5	

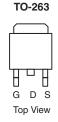
FEATURES

- TrenchFET® Power MOSFETS
- 175 °C Junction Temperature
- 100 % R_q and UIS Tested

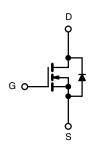


APPLICATIONS

- Power Supply
 - Secondary Synchronous Rectification
- Industrial



Ordering Information: SUM90N06-5m5P-E3 (Lead (Pb)-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	S T _C = 25 °C, unless oth	erwise noted			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	± 20	_ v	
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C	1-	90 ^d		
	T _C = 70 °C	I _D	90 ^d	^	
Pulsed Drain Current		I _{DM}	240	A	
Avalanche Current		I _{AS}	50		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ	
Maximum Power Dissipation ^a	T _C = 25 °C	В	272 ^b	w	
	T _A = 25 °C ^c	$ P_D$ $-$	3.75	VV	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.55	- C/W	

Notes:

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.

SUM90N06-5m5P

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Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	60			V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.5	\ \
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA
Zero Gate Voltage Drain Current		V _{DS} = 60 V, V _{GS} = 0 V			1	
	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	μА
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 150 °C			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	70			Α
	_	V _{GS} = 10 V, I _D = 20 A		0.0045	0.0055	Ω
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.0072	0.009	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		58		S
Dynamic ^b				•		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz		4700		pF
Output Capacitance	C _{oss}			620		
Reverse Transfer Capacitance	C _{rss}			250		
Total Gate Charge ^c	Q_g			78.5	120	nC
Gate-Source Charge ^c	Q_{gs}	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$		28		
Gate-Drain Charge ^c	Q_{gd}			20.6		
Gate Resistance	R_{g}	f = 1 MHz		1.2	2.4	Ω
Turn-On Delay Time ^c	t _{d(on)}			16	30	
Rise Time ^c	t _r	V_{DD} = 30 V, R_L = 0.6 Ω I_D \cong 50 A, V_{GEN} = 10 V, R_g = 1 Ω		10	20	ns
Turn-Off Delay Time ^c	t _{d(off)}			25	40	
Fall Time ^c	t _f			8	15	
Source-Drain Diode Ratings and Cha	racteristics T ₀	_C = 25 °C ^b		•		
Continuous Current	I _S				85	A
Pulsed Current	I _{SM}				240	
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.83	1.5	V
Reverse Recovery Time	t _{rr}			62	100	ns
Peak Reverse Recovery Current	I _{RM(REC)}	$I_F = 75 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		3.8	5.7	Α
Reverse Recovery Charge	Q _{rr}			118	180	nC

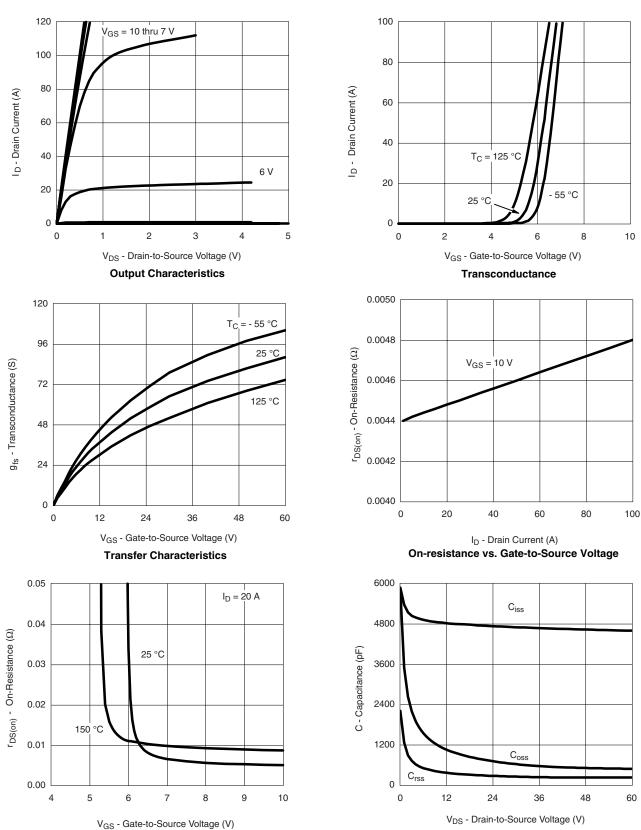
Notes:

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



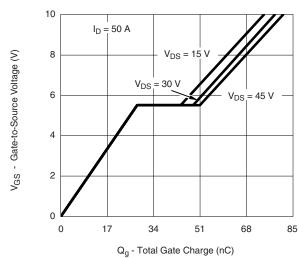
On-Resistance vs. Drain Current

Capacitance

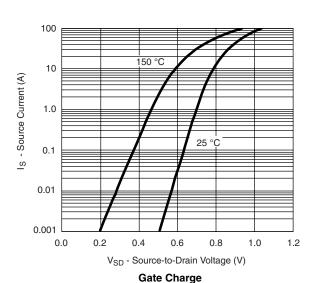
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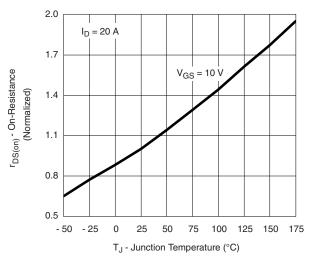
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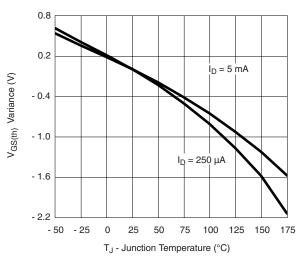
On-Resistance vs. Junction Temperature



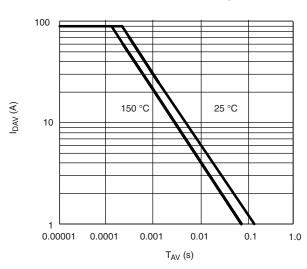
Source-Drain Diode Forward Voltage



Threshold Voltage



On-Resistance vs. Junction Temperature



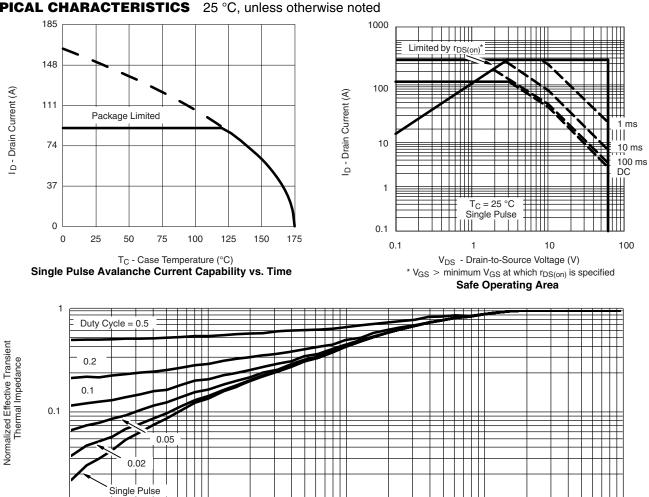
Maximum Drain Current vs. Case Temperature



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TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

10-3



Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

10-2

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